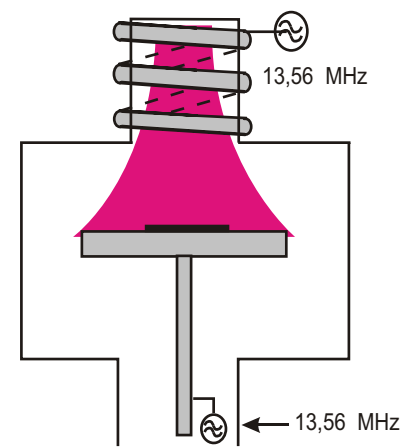
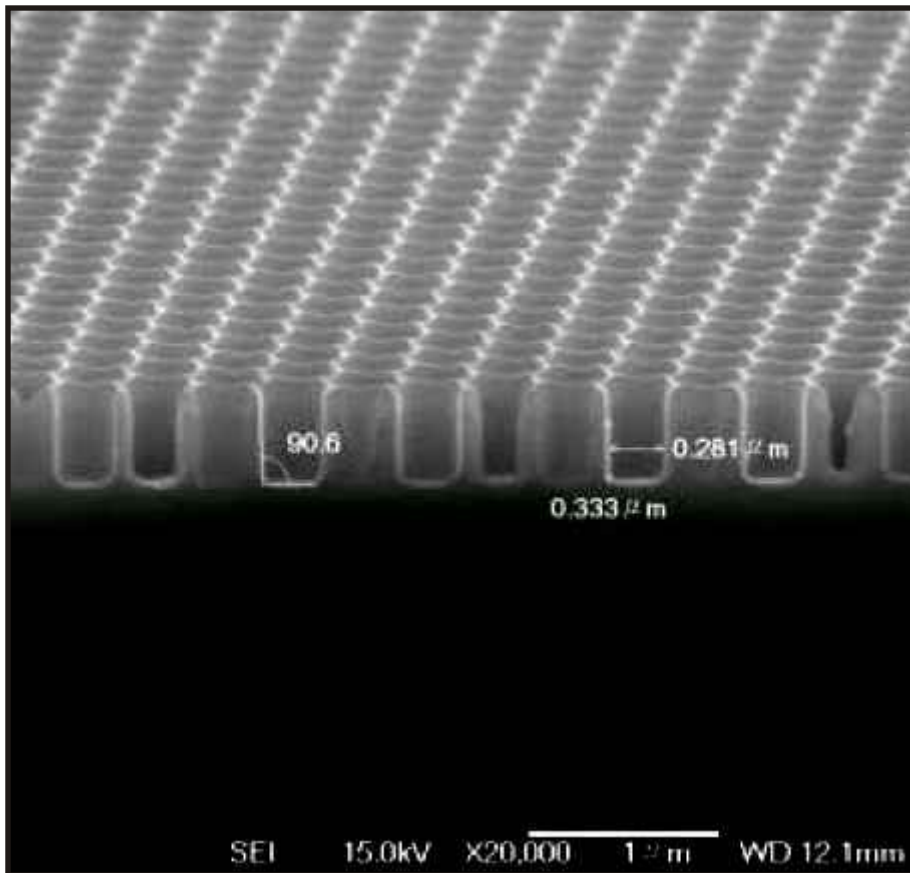


Plasmalab Data

GaAs/ AlGaAs Photonic Crystal ICP Etching



Plasmalab 80 Plus
Plasmalab System 100
Plasmalab System 133

Courtesy of NCTU:
top view of the 280 nm diameter holes
330 nm high, angle 90.6 °

Technology:

ICP - RIE
Cl based process

Results:

GaAs/ AlGas etch rate 130 nm/ min
selectivity to SiN 6: 1
highly anisotropic profile
uniform etch

